

HD74LS122

Retriggerable Monostable Multivibrator (with Clear)

REJ03D0428-0200

Rev.2.00

Feb.18.2005

This d-c triggered multivibrator features output pulse width control by three method. The basic pulse time is programmed by selection of external resistance and capacitance values. The HD74LS122 has internal timing resistor that allows the circuit to be used with only an external capacitor, if so desired. Once triggered, the basic pulse width may be extended by retriggering the gated low-level -active (A) or high-level active (B) inputs or be reduced by use of the overriding clear. Figure 1 illustrates pulse control by retriggering and early clear. This device is provided enough Schmitt hysteresis to ensure jitter-free triggering from the B input with transition rates as slow as 0.1 mV/ns.

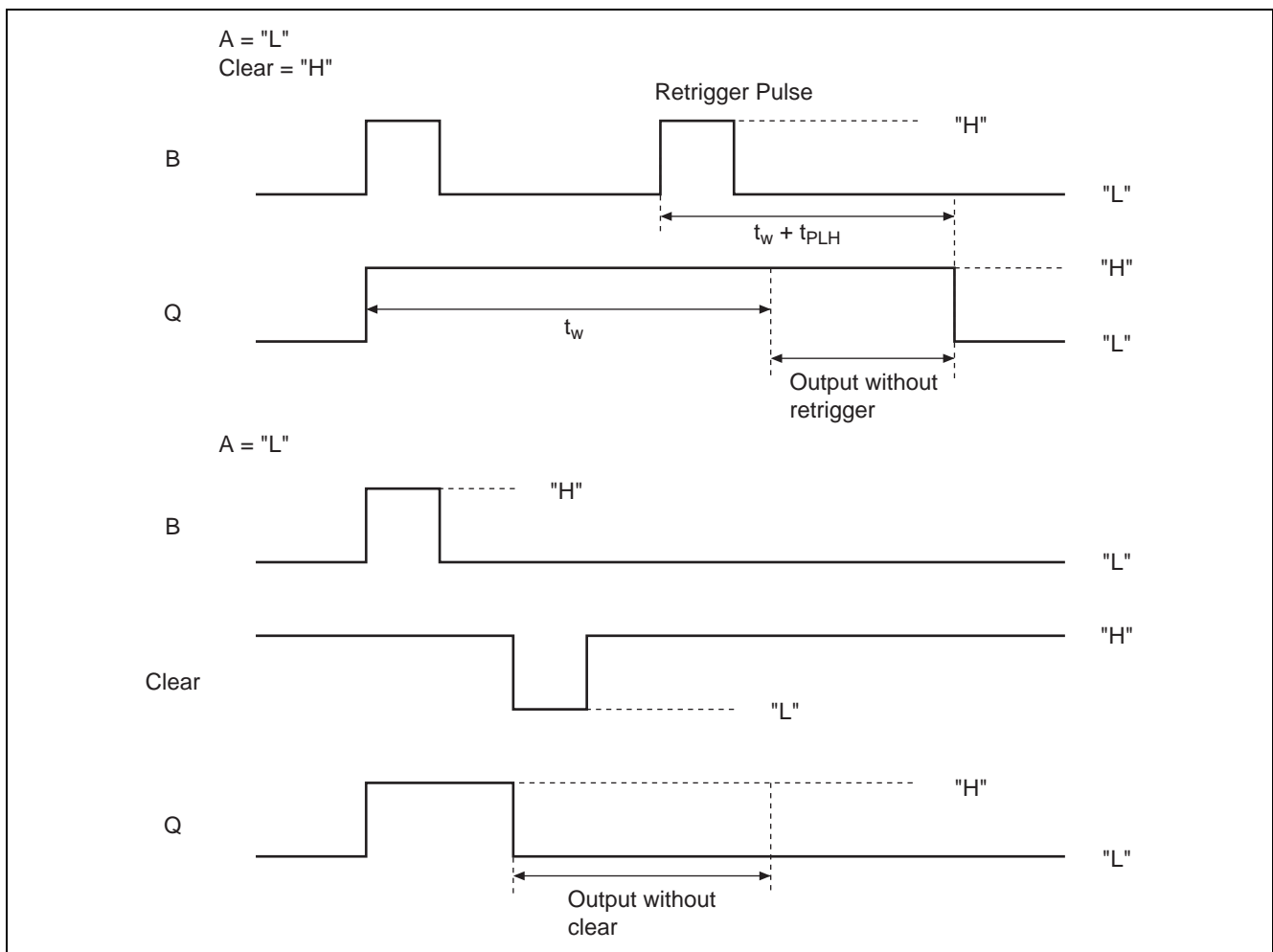


Figure 1 Typical Input / Output Pulse

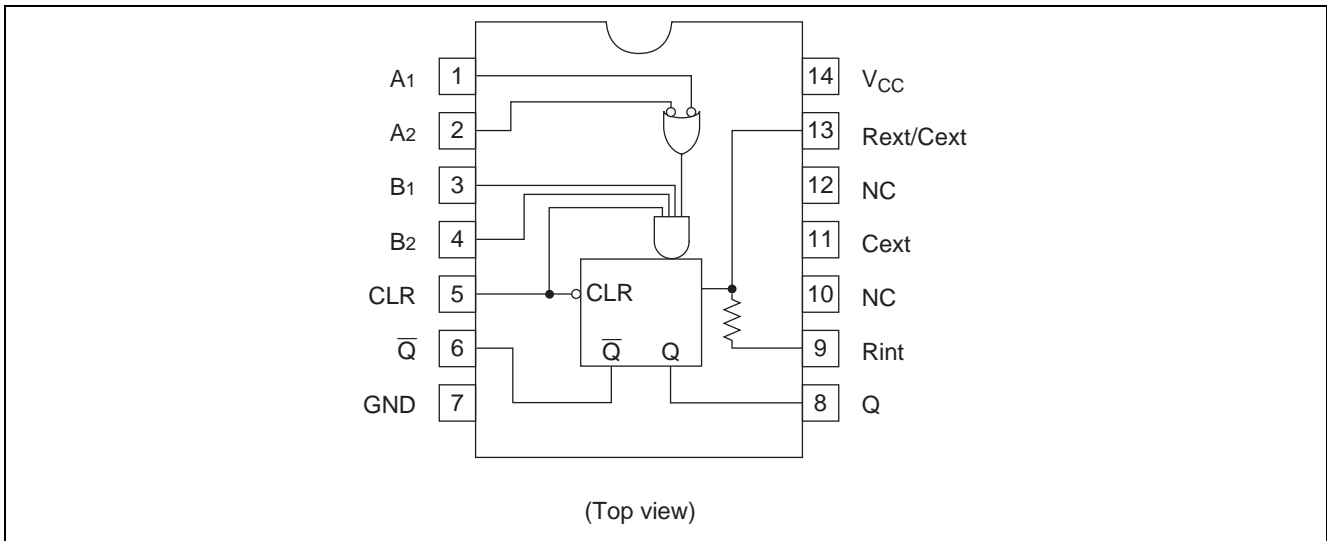
Features

- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LS122P	DILP-14 pin	PRDP0014AB-B (DP-14AV)	P	—
HD74LS122FPEL	SOP-14 pin (JEITA)	PRSP0014DF-B (FP-14DAV)	FP	EL (2,000 pcs/reel)

Note: Please consult the sales office for the above package availability.

Pin Arrangement



Function Table

Inputs					Outputs	
Clear	A ₁	A ₂	B ₁	B ₂	Q	\bar{Q}
L	X	X	X	X	L	H
X	H	H	X	X	L	H
X	X	X	L	X	L	H
X	X	X	X	L	L	H
H	L	X	↑	H	⌋	⌋
H	L	X	H	↑	⌋	⌋
H	X	L	↑	H	⌋	⌋
H	X	L	H	↑	⌋	⌋
H	H	↓	H	H	⌋	⌋
H	↓	↓	H	H	⌋	⌋
H	↓	H	H	H	⌋	⌋
↑	L	X	H	H	⌋	⌋
↑	X	L	H	H	⌋	⌋

Notes: H; high level, L; low level, X; irrelevant

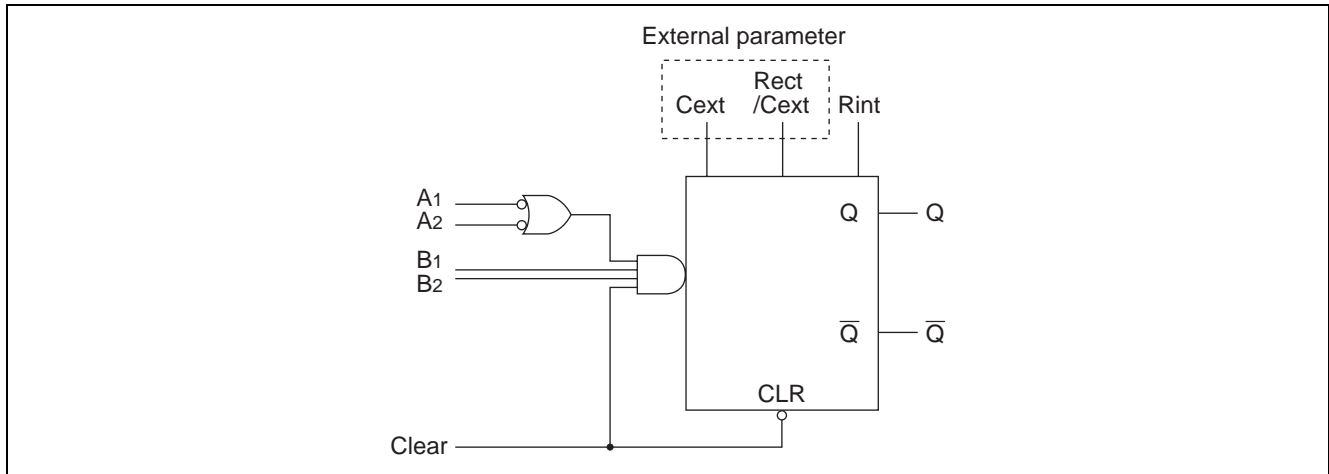
↑; transition from low to high level

↓; transition from high to low level

⌋; one high-level pulse

⌋; one low-level pulse

Block Diagram



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage	V_{CC}	7	V
Input voltage	V_{IN}	7	V
Power dissipation	P_T	400	mW
Storage temperature	T_{stg}	-65 to +150	°C

Note: Voltage value, unless otherwise noted, are with respect to network ground terminal.

Recommended Operating Conditions

Item	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	4.75	5.00	5.25	V
Output current	I_{OH}	—	—	-400	μA
	I_{OL}	—	—	8	mA
Operating temperature	T_{opr}	-20	25	75	°C
Input pulse width	t_w	40	—	—	ns
External timing resistance	R_{ext}	5	—	260	k Ω
External capacitance	C_{ext}	Non restriction			
Wiring capacitance at Rext/Cext terminal	R_{ext}/C_{ext}	—	—	50	pF

Electrical Characteristics

(Ta = -20 to +75 °C)

Item	Symbol	min.	typ.*	max.	Unit	Condition
Input voltage	V _{IH}	2.0	—	—	V	
	V _{IL}	—	—	0.8	V	
Output voltage	V _{OH}	2.7	—	—	V	V _{CC} = 4.75 V, V _{IH} = 2 V, V _{IL} = 0.8 V, I _{OH} = -400 μA
	V _{OL}	—	—	0.4	V	V _{CC} = 4.75 V, V _{IH} = 2 V, V _{IL} = 0.8 V
—		—	0.5			
Input current	I _{IH}	—	—	20	μA	V _{CC} = 5.25 V, V _I = 2.7 V
	I _{IL}	—	—	-0.4	mA	V _{CC} = 5.25 V, V _I = 0.4 V
	I _I	—	—	0.1	mA	V _{CC} = 5.25 V, V _I = 7 V
Short-circuit output current	I _{OS}	-20	—	-100	mA	V _{CC} = 5.25 V
Supply current**	I _{CC}	—	6	11	mA	V _{CC} = 5.25 V
Input clamp voltage	V _{IK}	—	—	-1.5	V	V _{CC} = 4.75 V, I _{IN} = -18 mA

* V_{CC} = 5 V, Ta = 25°C

** With all outputs open and 4.5 V applied to all data and clear inputs, I_{CC} is measured after a momentary ground, then 4.5 V, is applied to clock.

Note: To measure V_{OH} at Q, V_{OL} at \bar{Q} , or I_{OS} at Q, ground R_{ext} / C_{ext}, apply 2 V to B and clear, and pulse A from 2 V to 0 V.

Switching Characteristics

(V_{CC} = 5 V, Ta = 25°C)

Item	Symbol	Inputs	Outputs	min.	typ.	max.	Unit	Condition
Propagation delay time	t _{PLH}	A	Q	—	23	33	ns	C _{ext} = 0, R _{ext} = 5 kΩ, C _L = 15 pF, R _L = 2 kΩ
	t _{PHL}		\bar{Q}	—	32	45		
	t _{PLH}	B	Q	—	23	44		
	t _{PHL}		\bar{Q}	—	34	56		
	t _{PLH}	Clear	Q	—	20	27		
	t _{PHL}		\bar{Q}	—	28	45		
Output pulse width	t _{(out)min}	A or B	Q	—	116	200	μs	C _{ext} = 1000 pF, R _{ext} = 10 kΩ, C _L = 15 pF, R _L = 2 kΩ
	t _(out)		Q	4	4.5	5		

Typical Application Data for HD74LS122

For pulse widths when $C_{ext} \leq 1000$ pF, See Figure 3.

The output pulse is primarily a function of the external capacitor and resistor. For $C_{ext} > 1000$ pF, the output pulse width (t_w) is defined as: $t_{w(out)} = K \cdot R_{ext} \cdot C_{ext}$; See Figure 4.

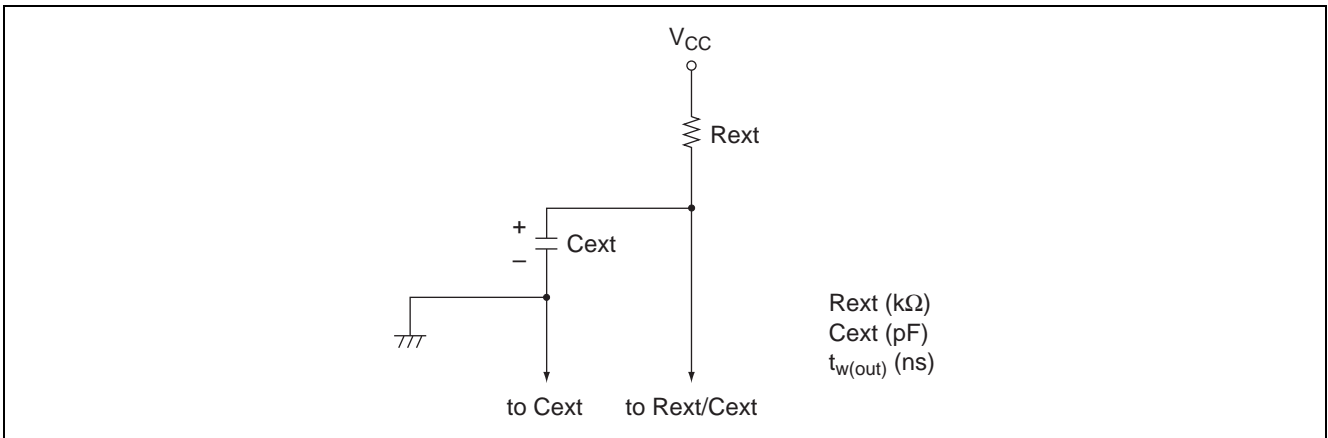


Figure 2 Timing Component Connections

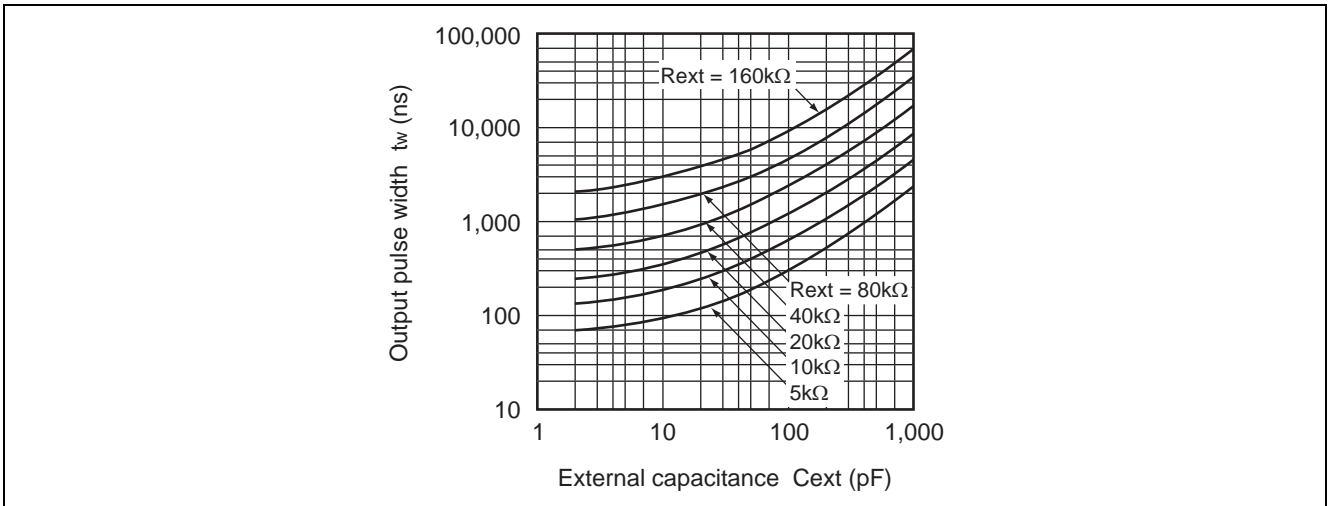


Figure 3 Typical Output Pulse Width ($C_{ext} \leq 1000$ pF)

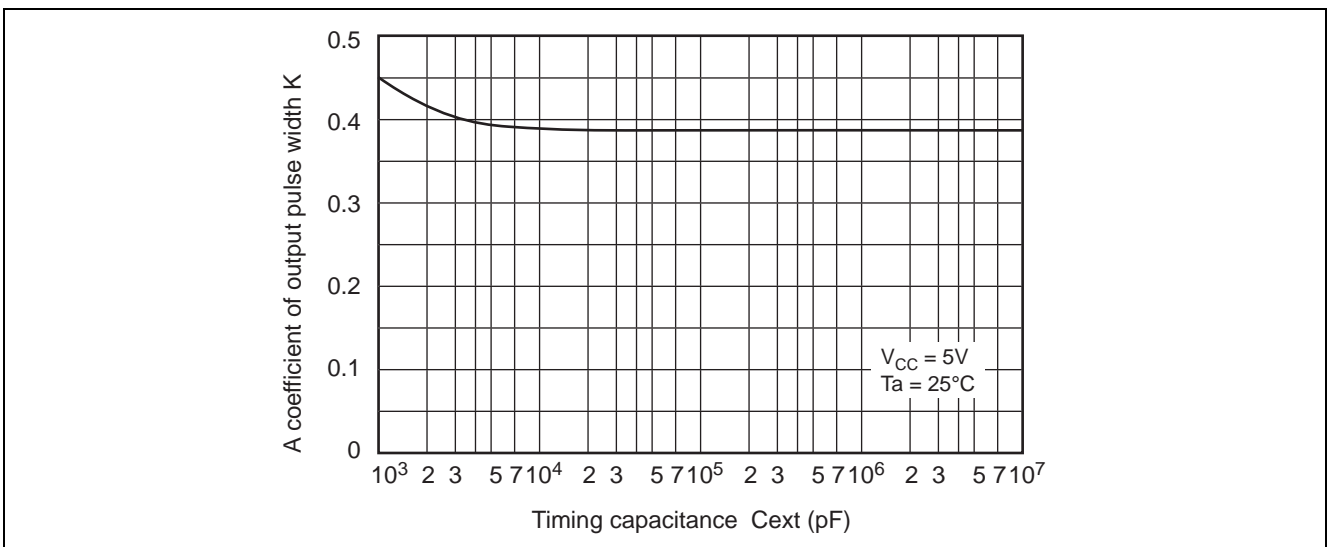
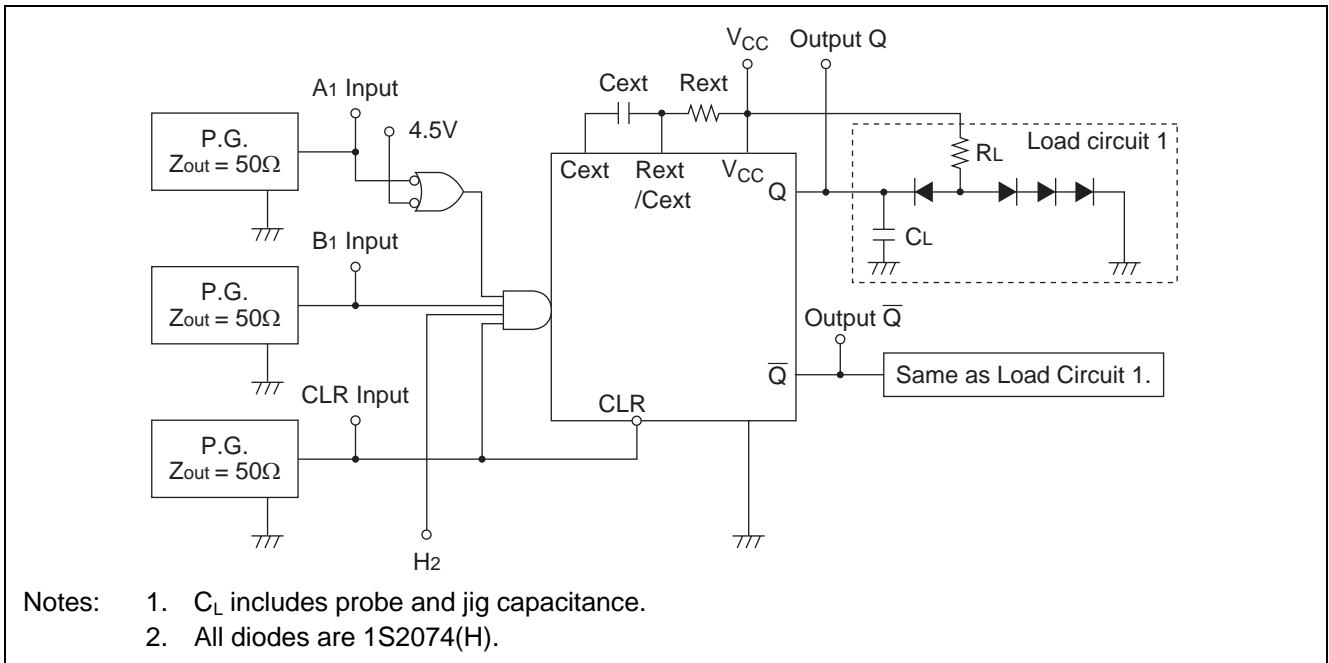


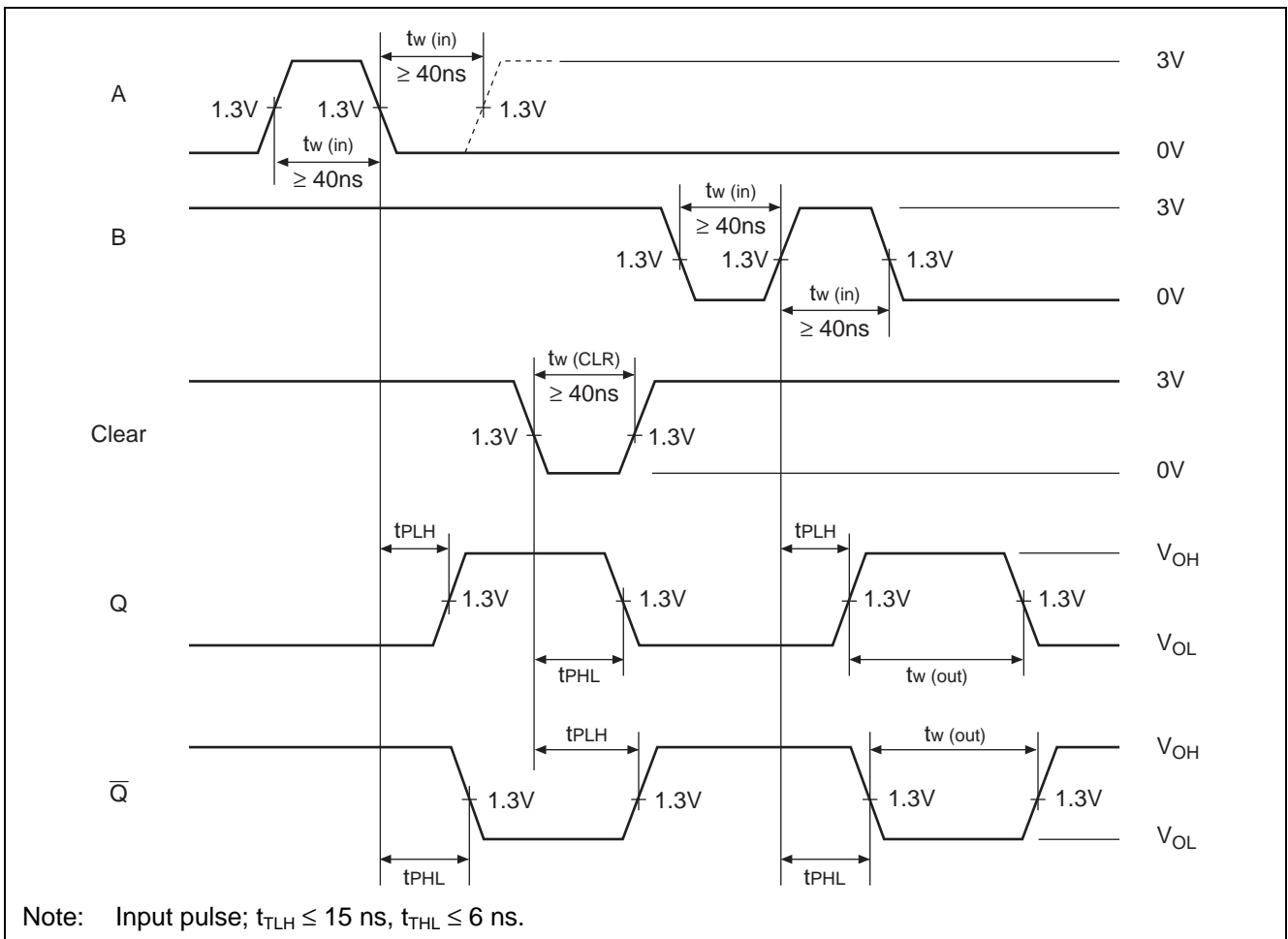
Figure 4 C_{ext} vs. K ($C_{ext} > 1000$ pF)

Testing Method

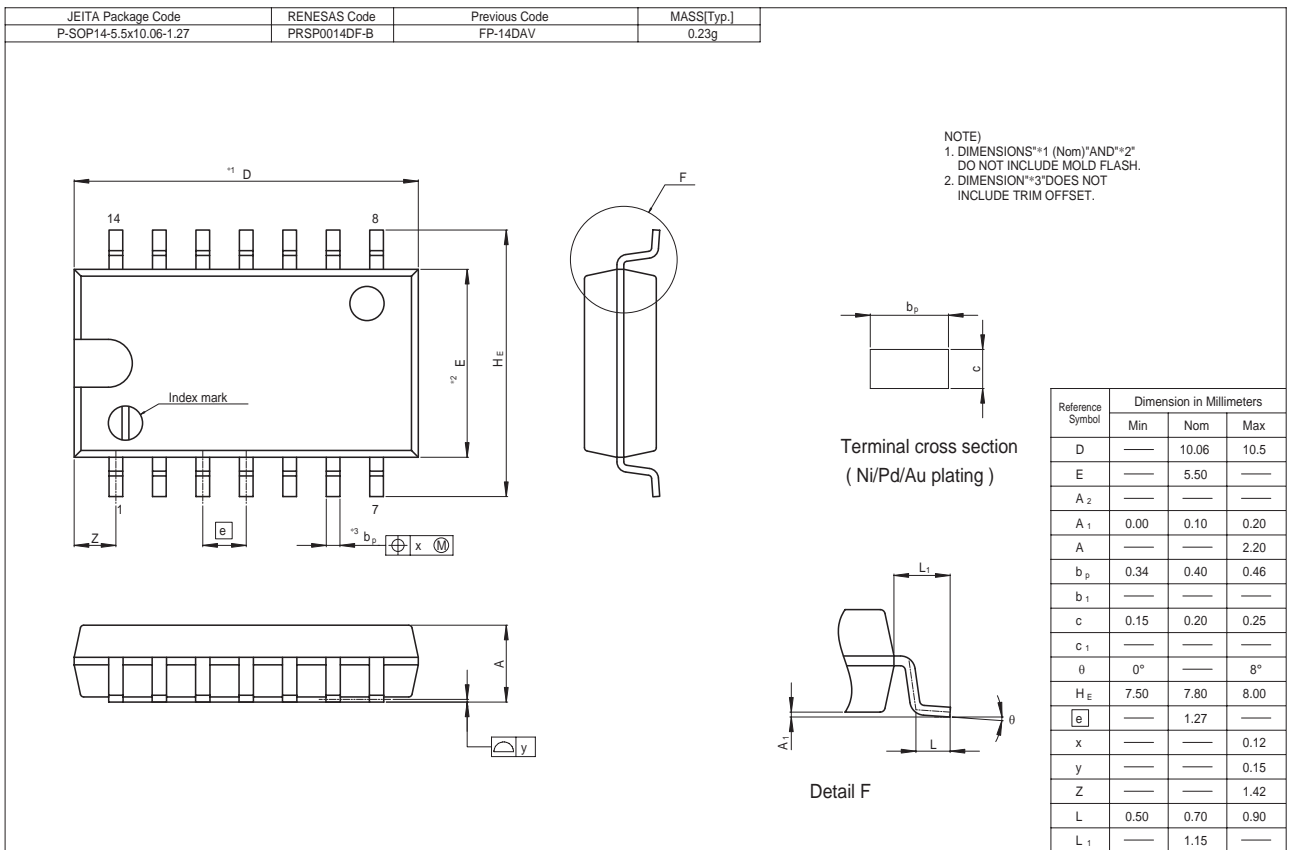
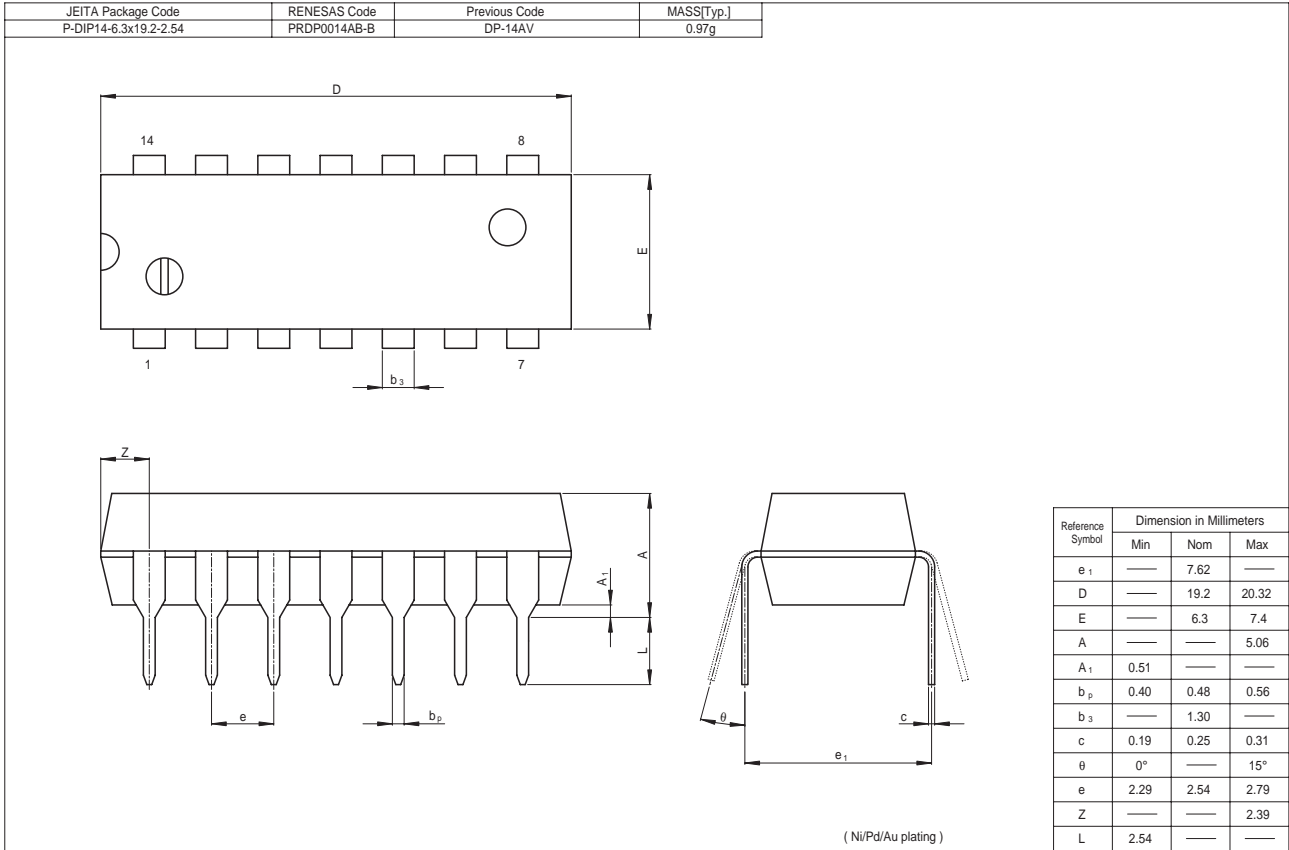
Test Circuit



Waveform



Package Dimensions



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